

Texture-Structure-Microstructure: a combined analysis by x-ray diffraction of $\text{Pb}_{0.76}\text{Ca}_{0.24}\text{TiO}_3$ / Pt / TiO_2 / SiO_2 / Si-(001)

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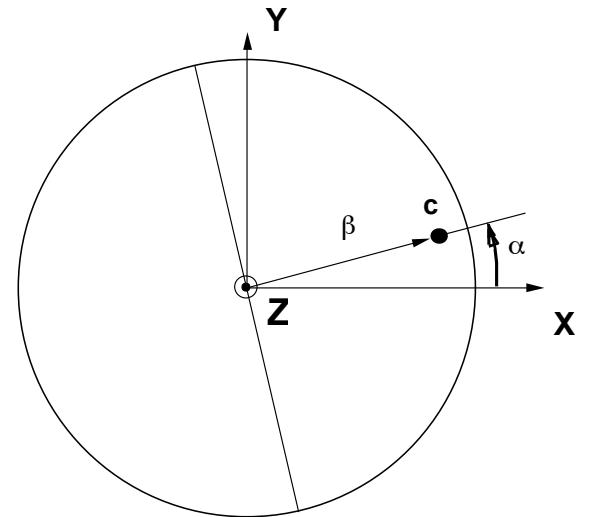
Summary

- Usual up-to-date approaches for polycrystals
 - Texture
 - Structure-Microstructure
 - Problems on ultrastructures
- Combined approach
 - Experimental needs
 - Methodology-Algorithm
 - Ultrastructure implementation
 - Case study on $\text{Pb}_{0.76}\text{Ca}_{0.24}\text{TiO}_3$
- Future trends

Usual Texture Analysis

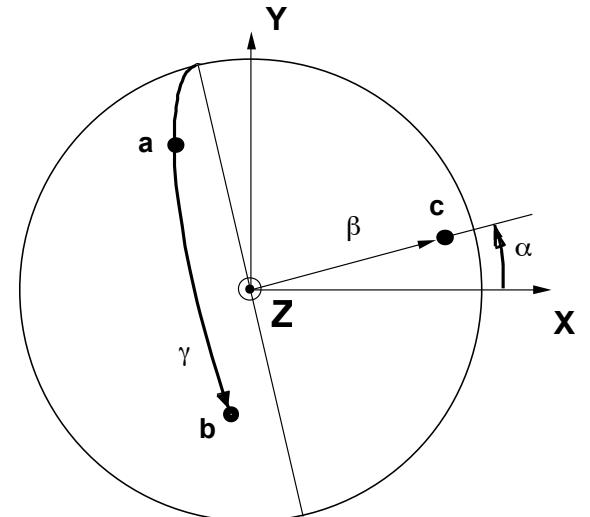
{hkl} pole figure measurement + corrections:

$$\frac{dV(\chi\phi)}{V} = \frac{1}{4\pi} P(\chi\phi) \sin\chi d\chi d\phi \rightarrow$$



We want $f(g)$ (ODF): with $g = (\alpha, \beta, \gamma)$

$$\frac{dV(g)}{V} = \frac{1}{8\pi^2} f(g) dg \rightarrow$$



We have to invert (Fundamental equation of Texture Analysis):

$$P_{hkl}(\vec{y}) = \frac{1}{2\pi} \int_{\langle hkl \rangle // \vec{y}} f(g) d\tilde{\varphi}$$

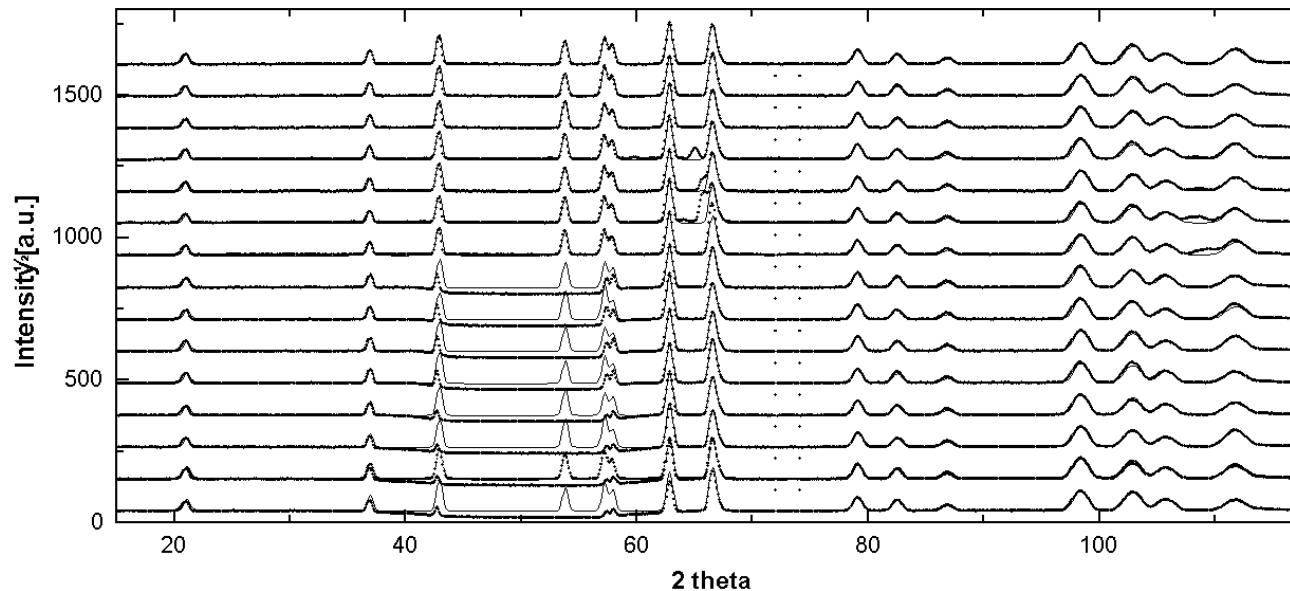


WIMV refinement method:
Williams-Imhof-Matthies-Vinel

$$f^{n+1}(g) = N \left[\frac{f^n(g) f^0(g)}{\prod_{hkl} \left(P_{hkl}^n(\vec{y}) \right)^{\frac{1}{I}}} \right]$$

Usual Structure-Microstructure Analysis (Full pattern fitting, Rietveld Analysis)

Si_3N_4 matrix with SiC whiskers:



Random powder: $I(2\theta) = \sum_{\text{hkl phases}} I_{\text{hkl, phases}}(2\theta)S_{\text{hkl, phases}}(2\theta) + \text{bkg}(2\theta)$

$$I_{hkl}(2\theta) = S |F_{hkl}|^2 m_{hkl} \frac{L_p}{V_c^2}$$

S: scale factor (**phase abundance**)

F_{hkl} : **structure** factor (includes Debye-Waller term)

V_c : **unit-cell** volume

$$S_{hkl}(2\theta) = S^I_{hkl}(2\theta) * S^S_{hkl}(2\theta)$$

S^I : instrumental broadening

S^S : Sample aberrations

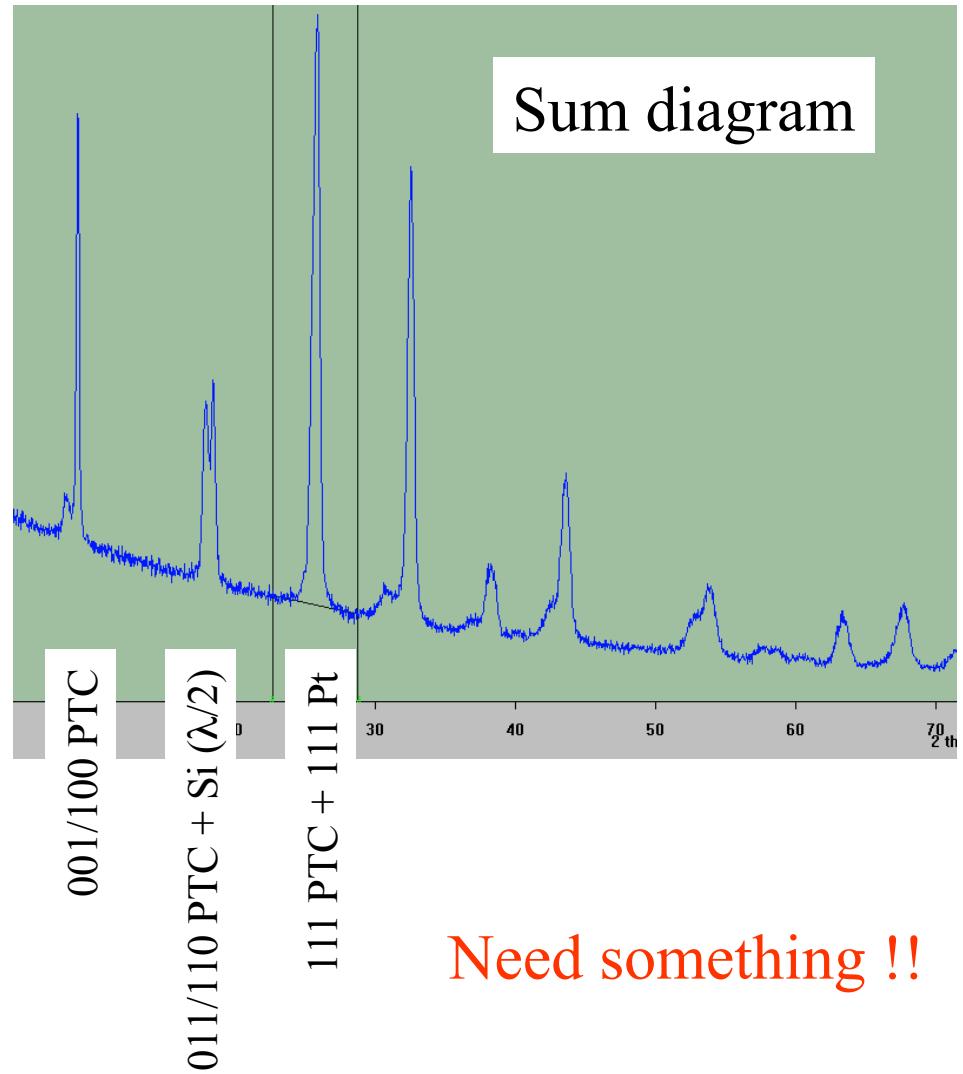
crystallite sizes (iso. or anisotropic)

rms microstrains ϵ

Problems on ultrastructures

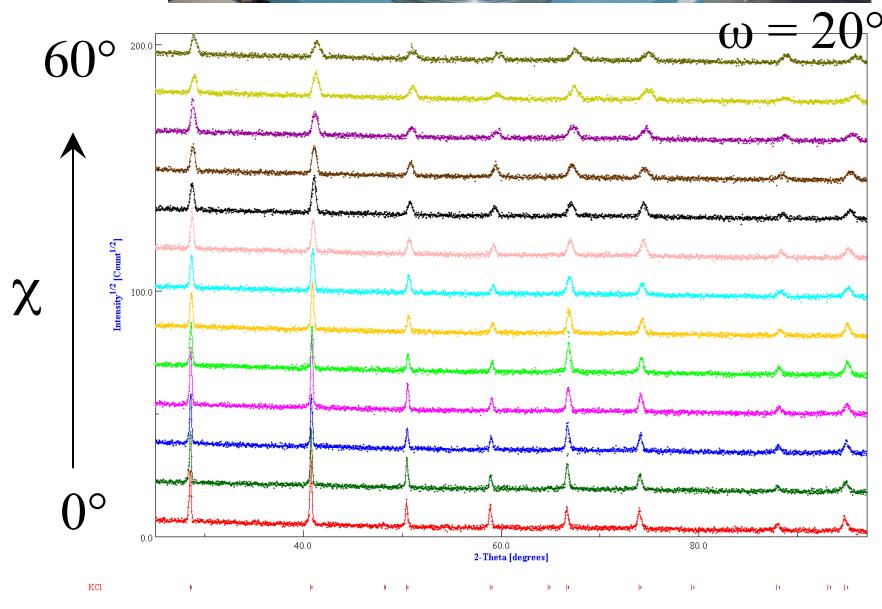
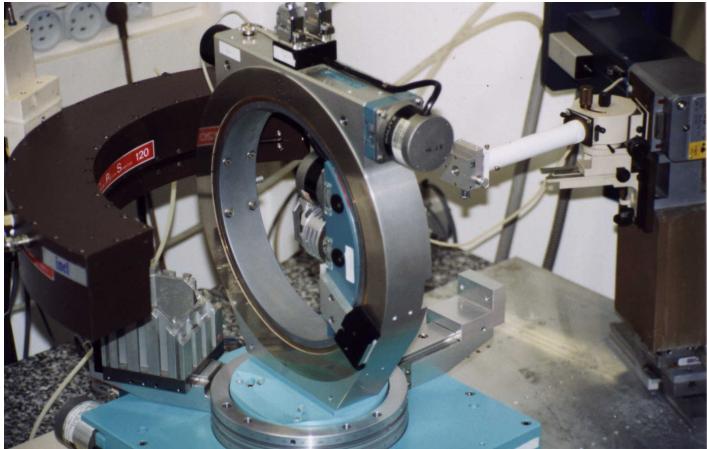
Ferroelectric film (PTC)
Electrode (Pt)
Antidiffusion barrier (TiO_2)
Oxide (native, thermally grown)
SC Substrate (Si)

- Strong intra- and inter-phase overlaps
- Mixture of very strong and lower textures
- texture effect not fully removable: ~~structure~~
- structure unknown: ~~texture~~



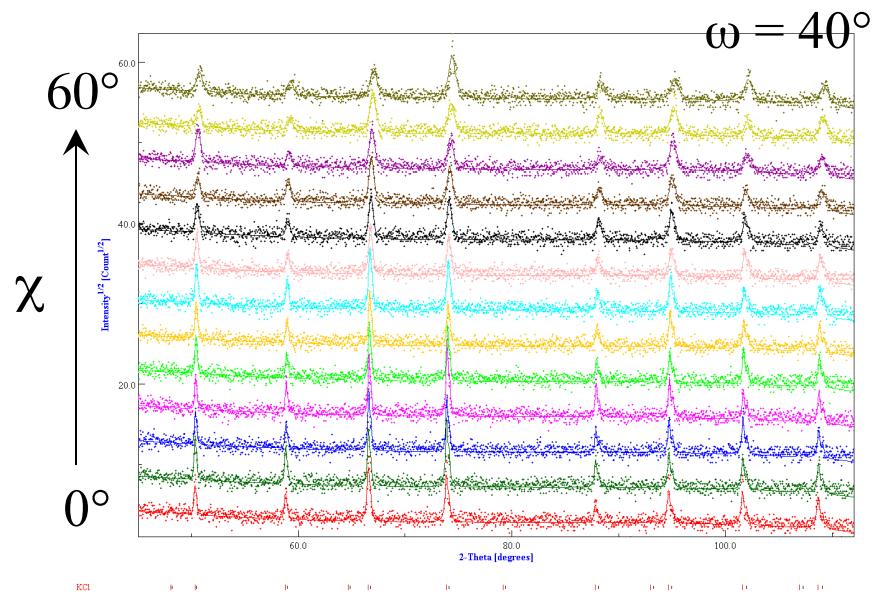
Combined approach

Experimental needs



Mapping Spectrometer space for correction of:

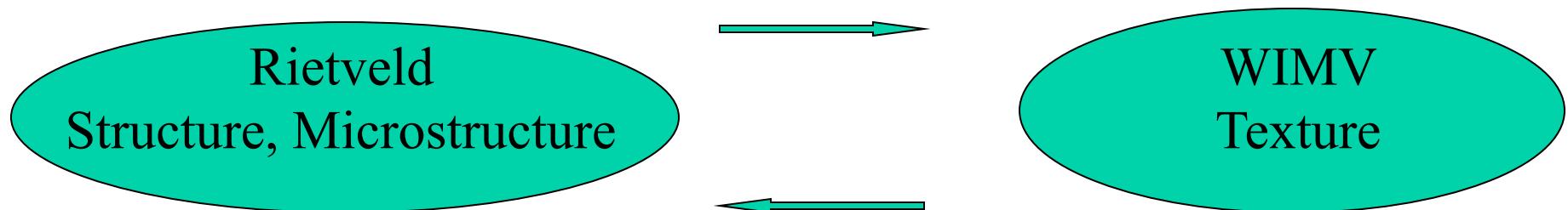
- instrumental resolution
- instrumental misalignments



Methodology-Algorithm

Correction of intensities for
texture:

$$I_{hkl}(2\theta, \chi, \varphi) = I_{hkl}(2\theta) P_{hkl}(\chi, \varphi)$$



Pole figure extraction (Le
Bail method): $P_{hkl}(\chi, \varphi)$

Rietveld and WIMV algorithm are alternatively used to correct for each others contributions: Marquardt non-linear least squares fit is used for the Rietveld.

Ultrastructure implementation

Corrections are needed for volumic/absorption changes when the samples are rotated. With a CPS detector, these correction factors are:

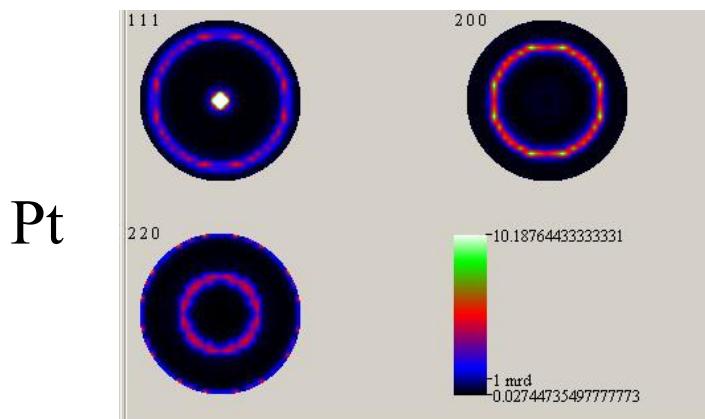
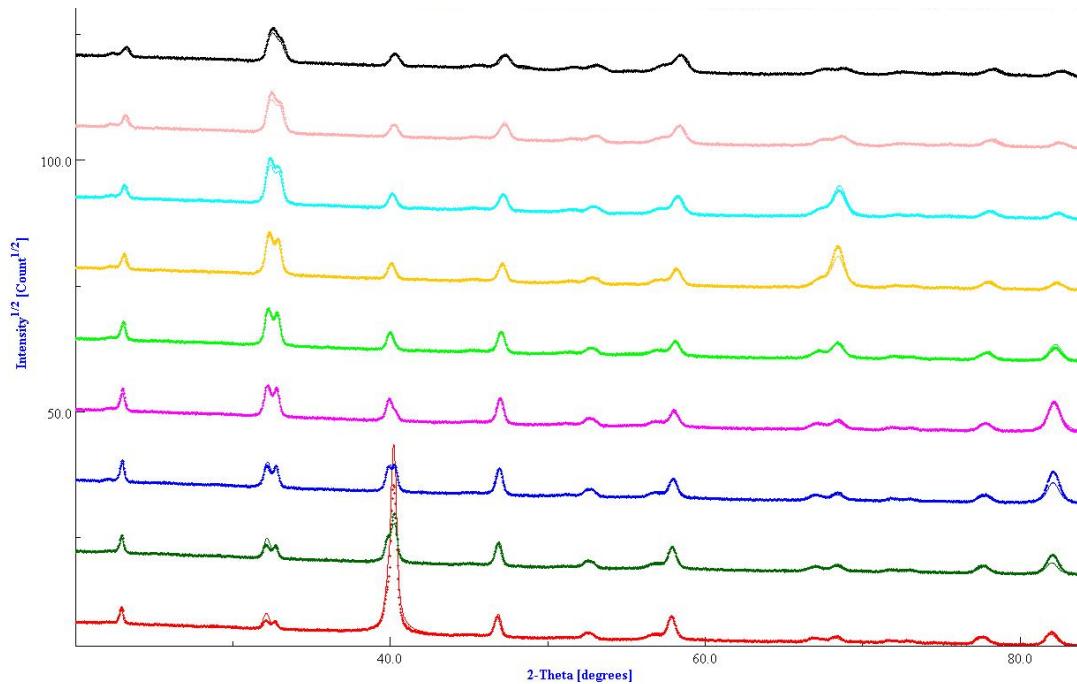
$$C_{\chi}^{\text{top film}} = g_1 \left(1 - \exp(-\mu T g_2 / \cos \chi) \right) / \left(1 - \exp(-2\mu T / \sin \omega \cos \chi) \right)$$

$$C_{\chi}^{\text{cov. layer}} = C_{\chi}^{\text{top film}} \left(\exp \left(-g_2 \sum \mu_i' T_i' / \cos \chi \right) \right) / \left(\exp \left(-2 \sum \mu_i' T_i' / \sin \omega \cos \chi \right) \right)$$

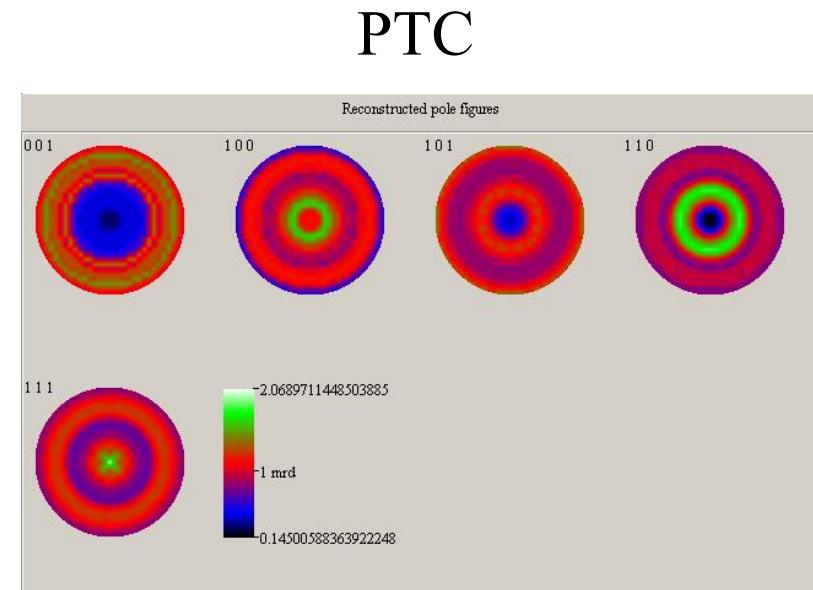


Gives access to individual Thicknesses
in the refinement

Case study on $\text{Pb}_{0.76}\text{Ca}_{0.24}\text{TiO}_3$

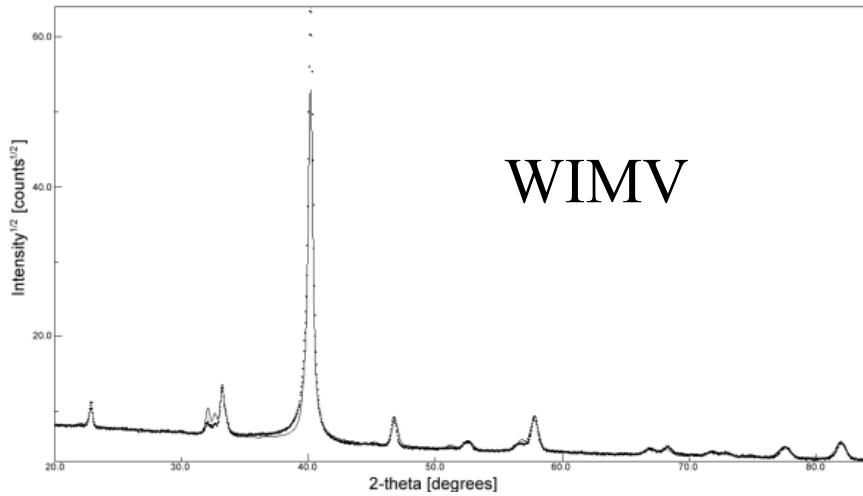


$a = 3.955(1)$ Å
 $T' = 462(4)$ Å
 $t'_{\text{iso}} = 458(3)$ Å
 $\varepsilon' = 0.0032(1)$

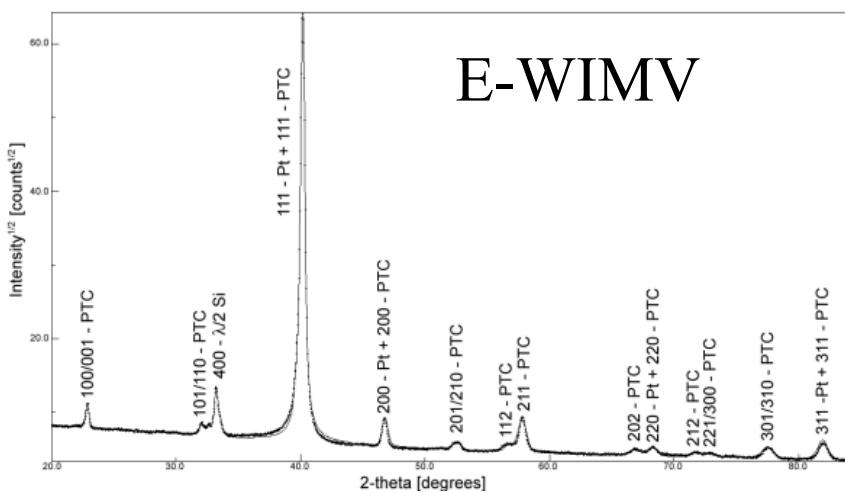


$a = 3.945(1)$ Å
 $c = 4.080(1)$ Å
 $T = 4080(10)$ Å
 $t_{\text{iso}} = 390(7)$ Å
 $\varepsilon = 0.0067(1)$

WIMV vs Entropy modified WIMV approach



WIMV



E-WIMV

Better refinement with E-WIMV:

- lower reliability factors (structure and texture)
- better high density level reproduction

Texture	Pt Texture Index (m.r.d. ²)	PTC Texture Index (m.r.d. ²)	Pt RP ₀ (%)	PTC RP ₀ (%)	Rw (%)	R _{Bragg} (%)
WIMV	48.1	1.3	18.4	11.4	12.4	7.7
EWIMV	40.8	2	13.7	11.2	7	4.7

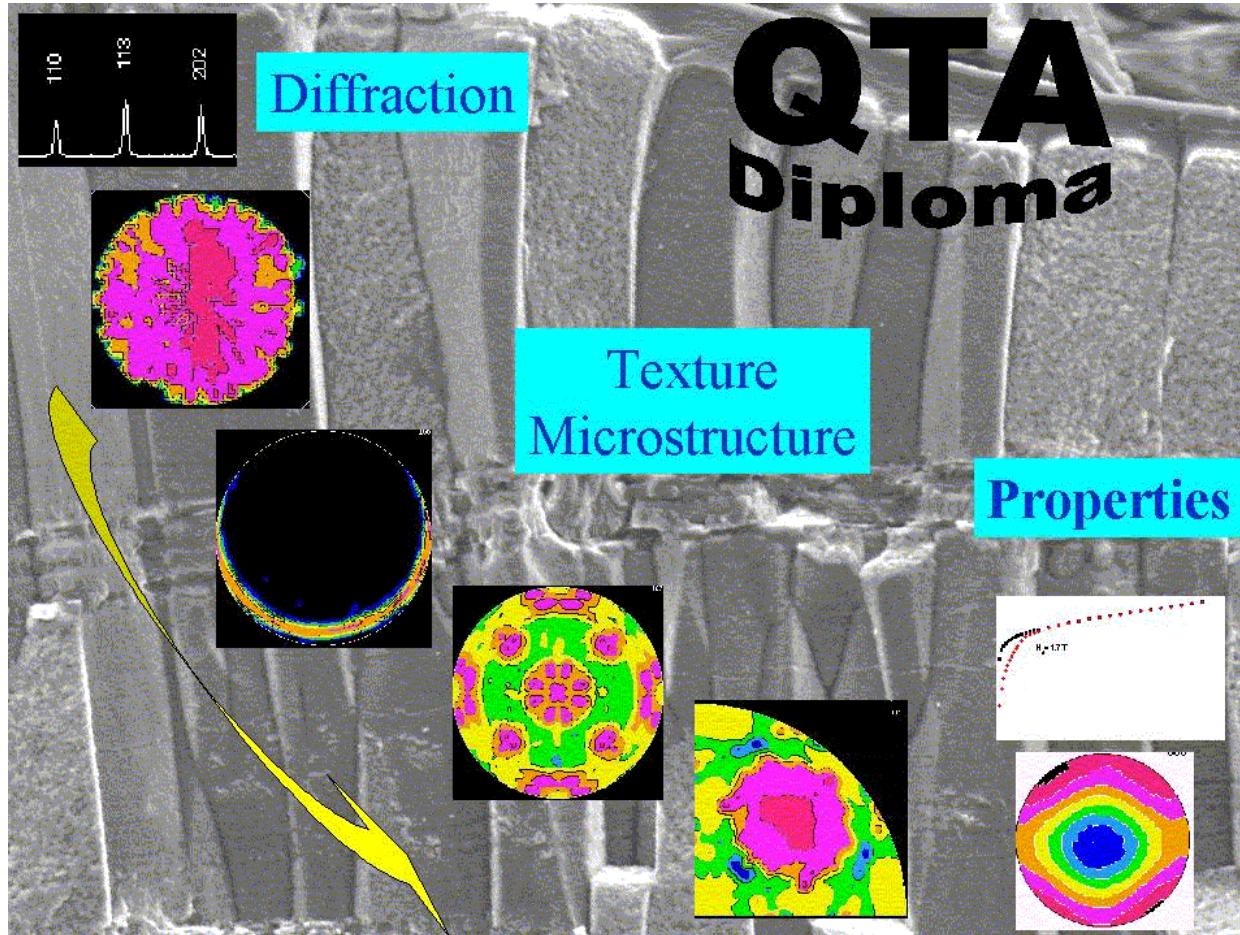
Future trends

- Combining with reflectivity measurements: independently measured and refined thicknesses, electron densities and roughnesses
- Adding residual stress determinations
- **Multiple Analysis Using Diffraction**, a web-based tutorial for the combined approach: search MAUD (Luca Lutterotti)
- **Quantitative Texture Analysis** Internet Course: <http://lpec.univ-lemans.fr/qta> (Daniel Chateigner)

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Quantitative Texture Analysis Internet Course



<http://lpec.univ-lemans.fr/qta>